GOSTONE

N-channel Power MOSFET:
30V, 4.2mohm, 44A

GN326B

Product Summary			
VDSS	VGSS	RDS(ON) TYP/MAX	ID MAX
30V	± 20V	4.2/5.6 mΩ@VGS=10V 6.7/11 mΩ@VGS=4.5V	**44A**

Features

- Low RDSon
- Low Gate Charge
- High Current Capacity
- Halogen-Free / RoHS Compliant

Application

- Battery Charging & Discharging for NB Battery Pack
- DC/DC Converters in Computing.

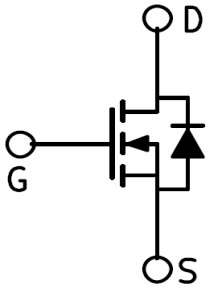
Marking Symbol Code

- Laser Marking Device Code: BJAH



GS : Gostone (fixed)
BJAH: Marking Device Code (fixed)
A: Factory Code
Y: Year Code
WW: Week Code
LT: LOT Code
○ : Pin#1 Identifier

Equivalent circuit



Form

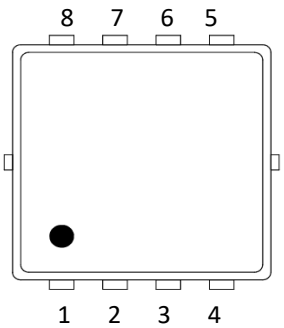
- Tape & Reel Embossed Type: 5,000pcs / reel

Absolute Maximum Rating Ta=25℃				
Parameter		Symbol	Rating	Unit
Drain to Source Voltage		VDS	30	V
Gate to Source Voltage		VGS	±20	V
Continuous Drain Current	Tc=25°C	ID	44	A
	Tc=100°C		28	A
Pulsed Drain Current*1		IDM	88	A
Continuous Drain Current	T_A=25°C	ID	13	A
	T_A=70°C		10	A
Avalanche Current		IAS	18	A
Avalanche Energy	L=0.1mH	EAS	16.2	mJ
Power Dissipation	Tc=25°C	PD	22.4	W
	Tc=100°C		8.9	W
Power Dissipation*3	T_A=25°C	PDSM	4.2	W
	T_A=70°C		2.7	W
Junction Temperature		Tj	150	℃
Storage Temperature		Tstg	-55 to +150	℃

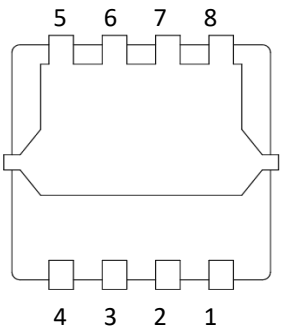
Thermal Characteristics (Typical)				
Parameter		Symbol	TYP	Unit
Junction-to Ambient (T_A=25°C)				
	t ≤ 10s	R_{thJA}*2	24.0	℃/W
	Steady-State		57.0	℃/W
Junction-to Case (Tc=25°C)				
	Steady-State	R_{thJC}	4.3	℃/W

*1Pulse width limited by maximum junction temperature.
*2The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.
*3The Power dissipation is based on R_{thJA} t ≤ 10s value.

Top View



Bottom View



1,2,3: Source
4: Gate
5,6,7,8: Drain

Electrical Characteristics (Tj=25degC)

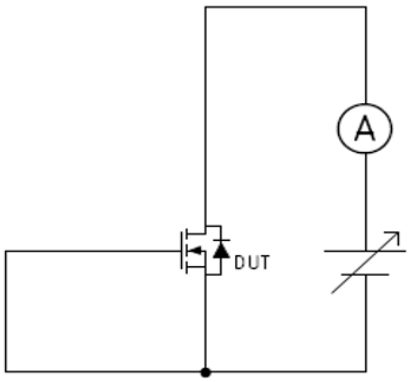
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	VDSS	ID=250μA, VGS=0V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS=24V, VGS=0V			1	μA
Gate-Source Leakage Current	IGSS	VGS=±20V, VDS=0V			±100	nA
Gate-Source Threshold Voltage	Vth	VDS=VGS, ID=250μA	1.10	1.45	2.40	V
Drain-Source On-State Resistance	RDS(on)1 RDS(on)2	ID=13A, VGS=10V ID=13A, VGS=4.5V		4.2 6.7	5.6 11.0	mΩ
Forward Transconductance	gFS	VGS=5V, ID=13A		14		S
Input Capacitance *1 Output Capacitance *1 Reverse Transfer Capacitance *1	Ciss Coss Crss	VDS=15V, VGS=0V, f=1MHz		768 553 31		pF
Gate Resistance *1	Rg	f=1MHz		1.2		Ω
Turn-On Delay Time *1 *2 Rise Time *1 *2	td(on) tr	VDD=15V, VGS=10V, ID=13A		3.1 2.6		ns
Turn-Off Delay Time *1 *2 Fall Time *1 *2	td(off) tf	VDD=15V, VGS=10V, ID=13A		12.4 5.2		ns
Total Gate Charge *1 Gate-Source Charge *1 Gate-Drain Charge *1	Qg Qgs Qgd	VDD=15V, VGS=10V, ID=13A		15.2 2.3 3.5		nC
Diode Forward Voltage	VSD	IS=13A, VGS=0V			1.2	V
Maximum Body Diode Continuous Current	IS				18.6	A
Body Diode Reverse Recovery Time *1 Body Diode Reverse Recovery Charge *1	trr Qrr	IF=13A, di/dt=100A/μs		23.0 10.0		ns nC

Note *1 Guaranteed by Design

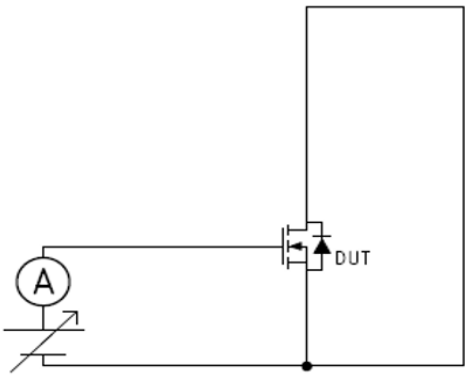
Note *2 Measurement Circuit for Switching Characteristics

Test circuits

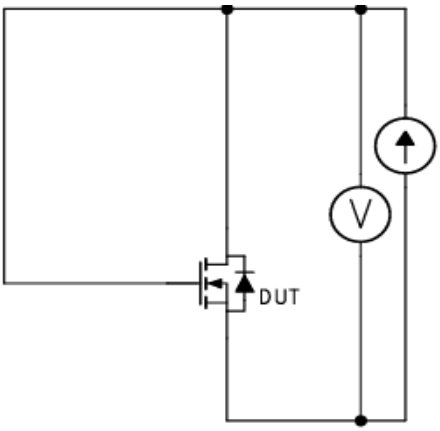
Test Circuit 1
VDSS/IDSS



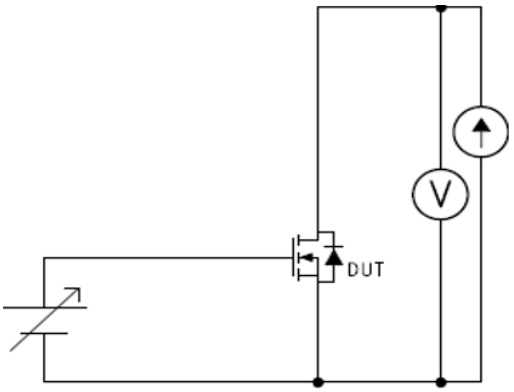
Test Circuit 2
IGSS



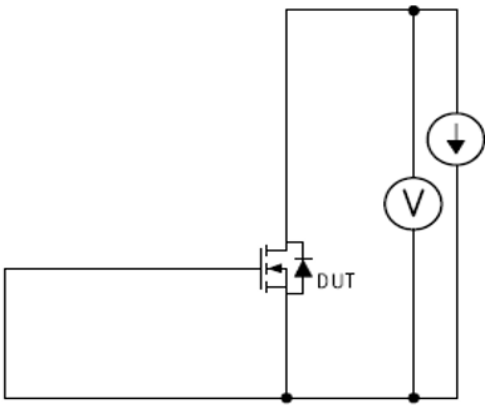
Test Circuit 3
Vth



Test Circuit 4
RDS(on)

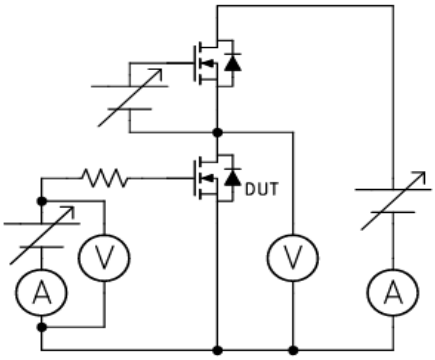


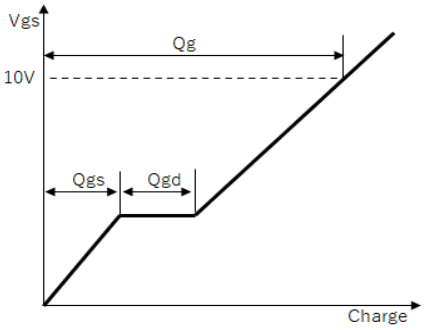
Test Circuit 5
VF



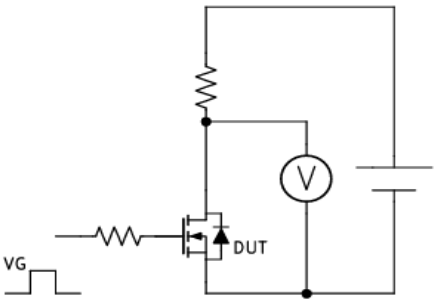
Test circuits

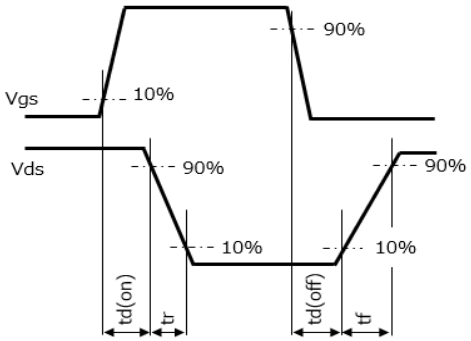
Test Circuit 6
Qg



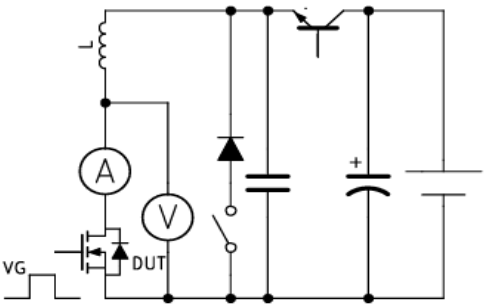


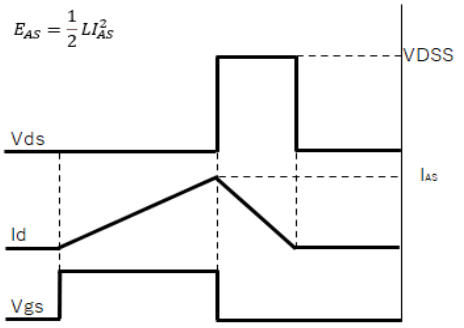
Test Circuit 7
Swiching Tim



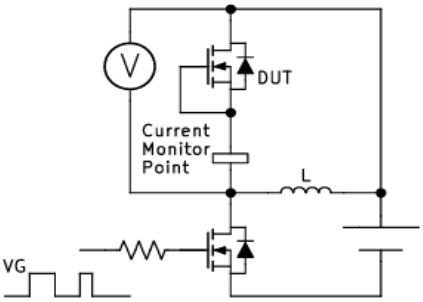


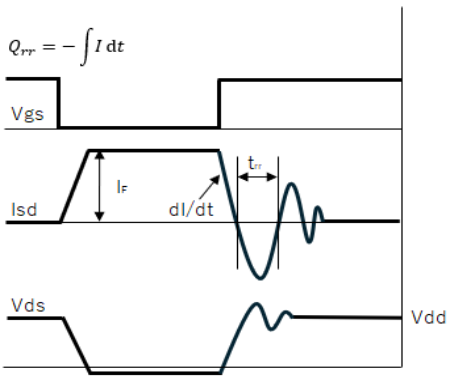
Test Circuit 8
IAS





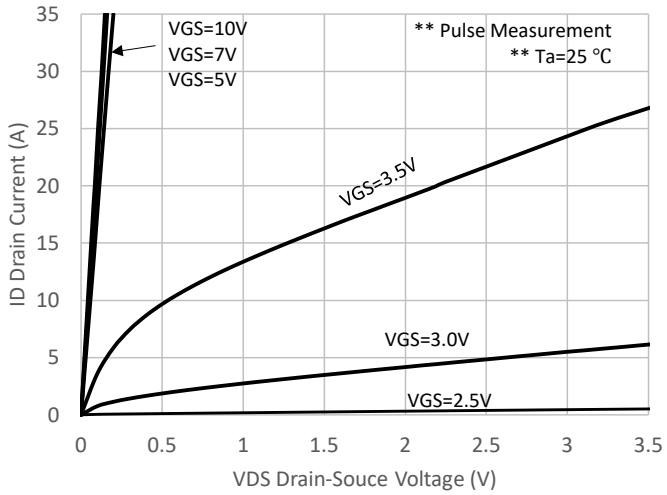
Test Circuit 9
trr/Qrr



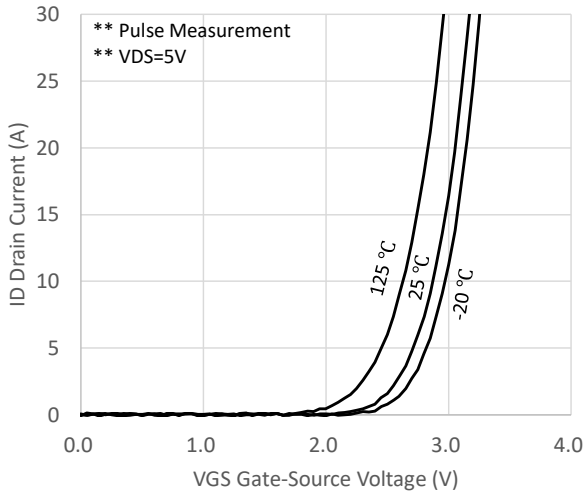


Technical data

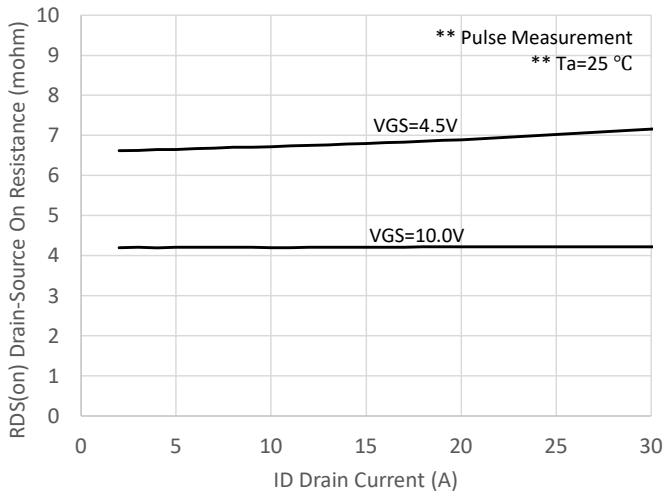
ID to VDS



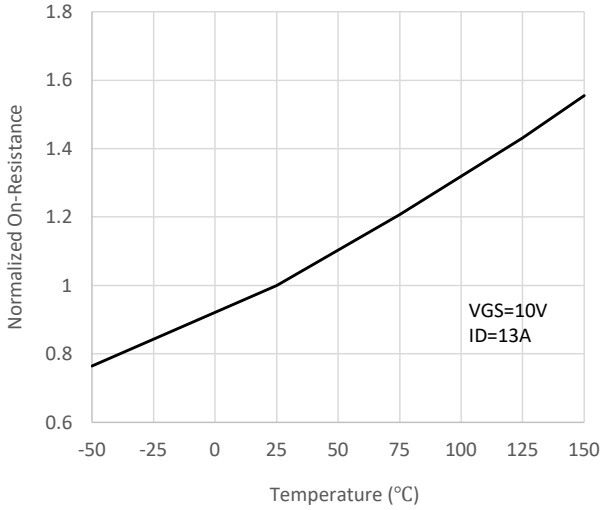
ID to VGS



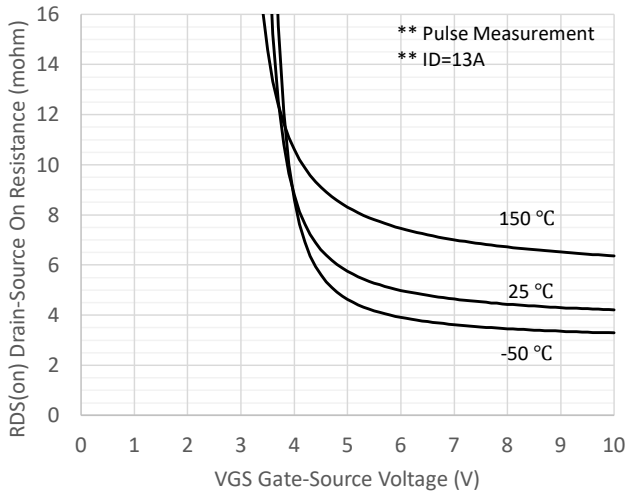
RDS(on) to ID



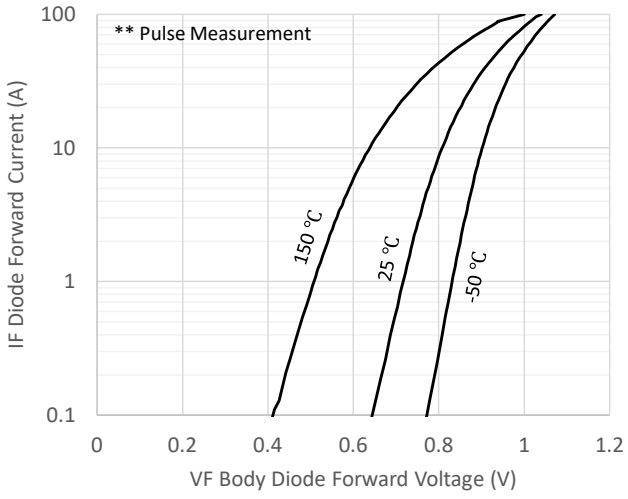
On-Resistance vs Junction Temperature



RDS(on) to VGS

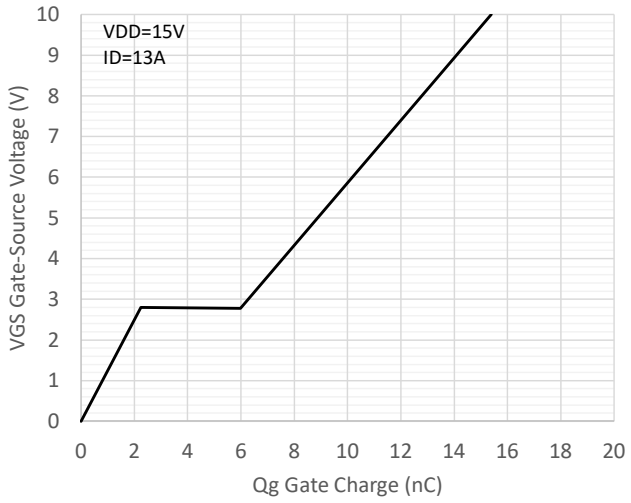


IF to VF

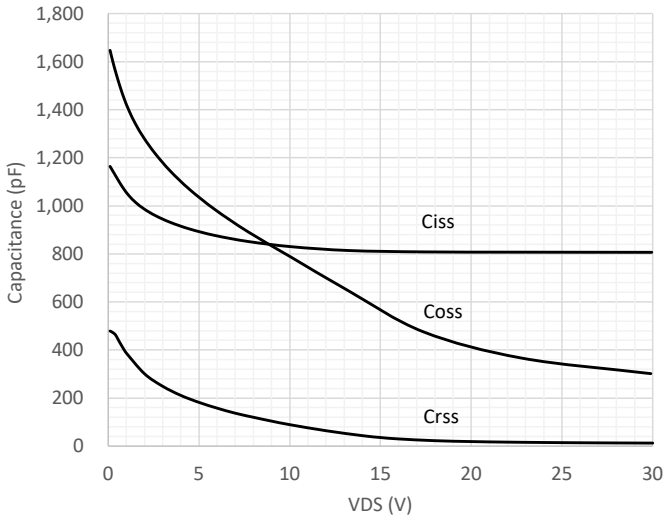


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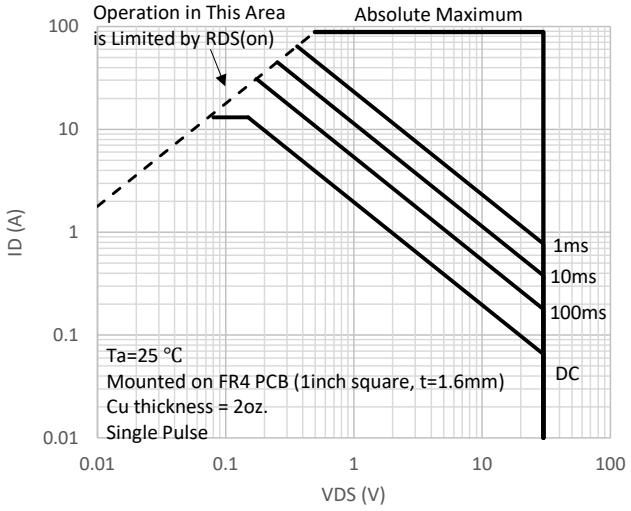
Gate-Charge Characteristics



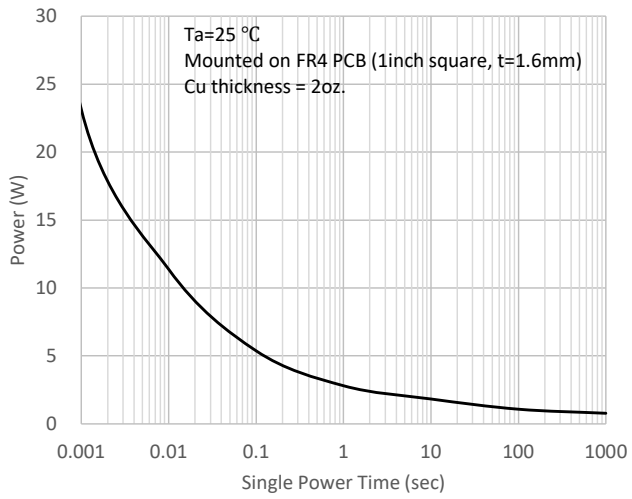
Capacitance Characteristic



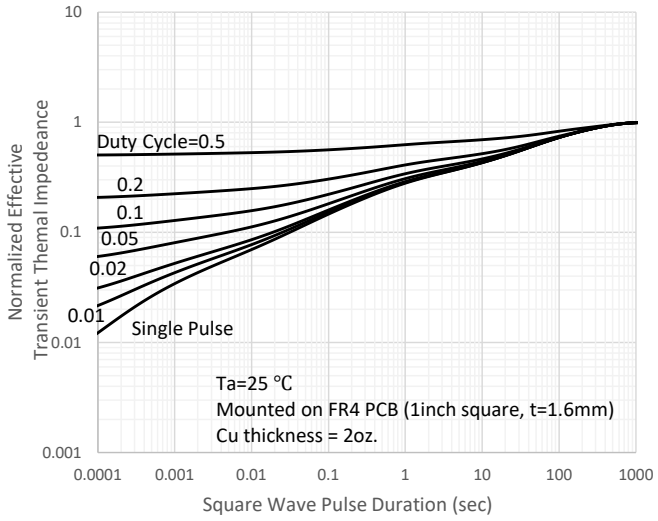
SOA



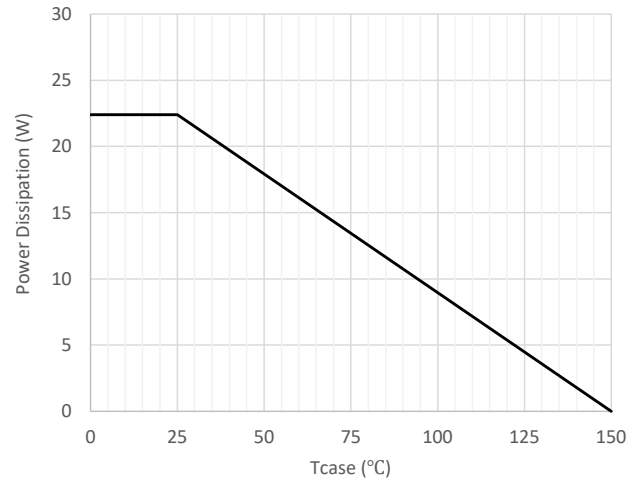
Single Pulse Maximum Power Dissipation



Thermal Response

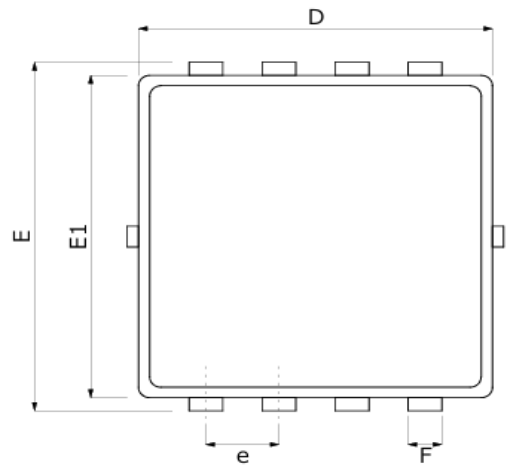


Power Derating

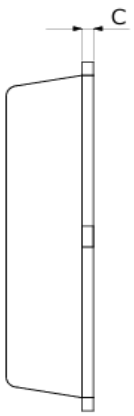


Package Outline Dimensions

Top View

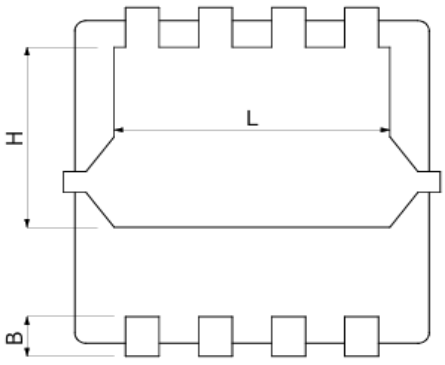


Side View





Bottom View

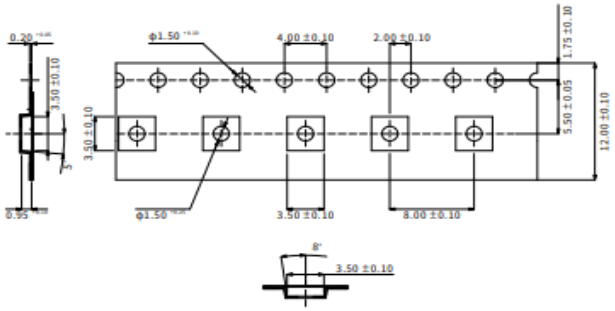


Symbol	Min	Typ	Max
A	0.725	0.775	0.825
B	0.28	0.38	0.48
C	0.13	0.15	0.20
D	3.05	3.15	3.25
D1			0.10
E	3.25	3.35	3.45
E1	3.0	3.1	3.2
e	0.60	0.65	0.70
F	0.25	0.30	0.35
H	1.48	1.58	1.68
L	2.35	2.45	2.55

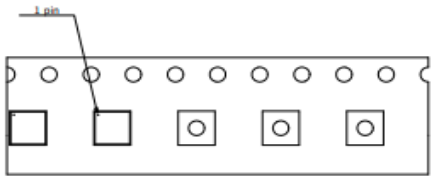
Form

- Tape & Reel Embossed Type: 5,000pcs / reel
- Factory PKG Code: PDFN
- Tape Width: 12mm, Pitch: 8mm, Reel Size: 12inch

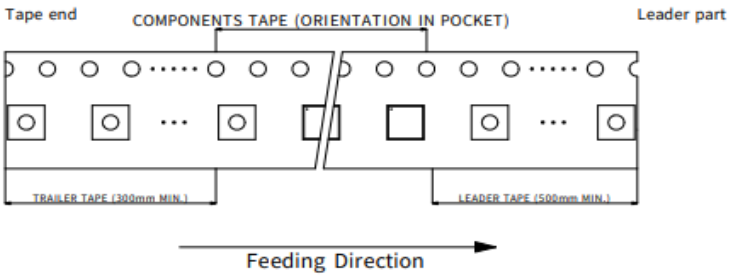
Tape size (mm)



Pin1 Direction



Tape end ~ Leader part (mm)



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